METHOD OF FORMING CONTACT PLUG ON SILICIDE STRUCTURE

ABSTRACT

A method of manufacturing a semiconductor device is provided. A semiconductor element is formed on a substrate. The semiconductor element has at least one nickel silicide contact region, an etch stop layer formed over said element, and an insulating layer formed over said etch stop layer. A portion of the etch stop layer immediately over a selected contact region is removed using a process that does not substantially react with the contact region, to form a contact opening. The contact opening is then filled with a conductive material to form a contact.

FIG. 2A